

B¹
(contd)
possible to obtain a V-groove, which has the side as (111) B face as in the case where HC1 is used.

IN THE CLAIMS:

Please amend[✓] claims 34, 35 and 47 as follows:

B²
34. (Amended) A light emitting semiconductor device according to claim 33, wherein an optical guiding layer having refractive index lower than that of said active layer and higher than that of a cladding layer inside the V-groove is provided between said active layer and said cladding layer inside the V-groove.

35. (Amended) A light emitting semiconductor device according to claims 33 or 34, wherein said first cladding layer and said first optical guiding layer are of the same first conductivity type, said cladding layer inside the V-groove and said optical guiding layer are of the same second conductivity type, and said cladding layer outside the V-groove is of second conductivity type or has high resistance.

B³
47. (Amended) A semiconductor device according to claim 43, wherein an energy gap of the cladding layer outside said V-groove is greater than an energy gap of the cladding layer inside said V-groove.
